N-Channel Silicon MOSFET

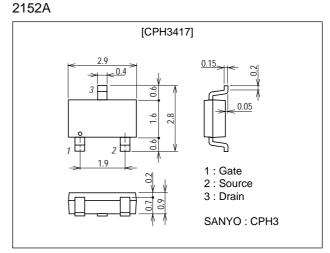


Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 1.8V drive.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	۱D		1.8	A
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	7.2	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	0.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +125	°C

Electrical Characteristics at Ta=25°C

Symbol	Conditions	Ratings			Unit
		min	typ	max	Unit
V(BR)DSS	ID=1mA, VGS=0	20			V
IDSS	VDS=20V, VGS=0			1	μA
IGSS	V _{GS} =±8V, V _{DS} =0			±10	μΑ
VGS(off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
yfs	VDS=10V, ID=1A	1.9	2.8		S
R _{DS} (on)1	ID=1A, VGS=4V		160	210	mΩ
R _{DS} (on)2	ID=0.5A, VGS=2.5V		200	280	mΩ
RDS(on)3	ID=0.1A, VGS=1.8V		280	390	mΩ
	V(BR)DSS IDSS IGSS VGS(off) yfs RDS(on)1 RDS(on)2	V(BR)DSS ID=1mA, VGS=0 IDSS VDS=20V, VGS=0 IGSS VGS=16V, VDS=0 VGS(off) VDS=10V, ID=1mA yfs VDS=10V, ID=1A RDS(on)1 ID=1A, VGS=4V RDS(on)2 ID=0.5A, VGS=2.5V	V(BR)DSS ID=1mA, VGS=0 20 IDSS VDS=20V, VGS=0 20 IGSS VGS=48V, VDS=0 20 VGS(off) VDS=10V, ID=1mA 0.4 yfs VDS=10V, ID=1A 1.9 RDS(on)1 ID=1A, VGS=4V 20 RDS(on)2 ID=0.5A, VGS=2.5V 20	Symbol Conditions min typ V(BR)DSS ID=1mA, VGS=0 20 20 IDSS VDS=20V, VGS=0 20 20 IGSS VGS=±8V, VDS=0 20 20 VGS(off) VDS=10V, ID=1mA 0.4 20 yfs VDS=10V, ID=1A 1.9 2.8 RDS(on)1 ID=1A, VGS=4V 160 200 RDS(on)2 ID=0.5A, VGS=2.5V 200 200	Symbol Conditions min typ max V(BR)DSS ID=1mA, VGS=0 20 1 IDSS VDS=20V, VGS=0 1 1 IGSS VGS=±8V, VDS=0 1 ±10 VGS(off) VDS=10V, ID=1mA 0.4 1.3 yfs VDS=10V, ID=1A, VGS=4V 1.9 2.8 RDS(on)1 ID=1A, VGS=4V 160 210 RDS(on)2 ID=0.5A, VGS=2.5V 200 280

Marking : KS

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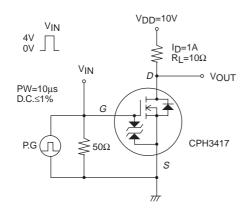
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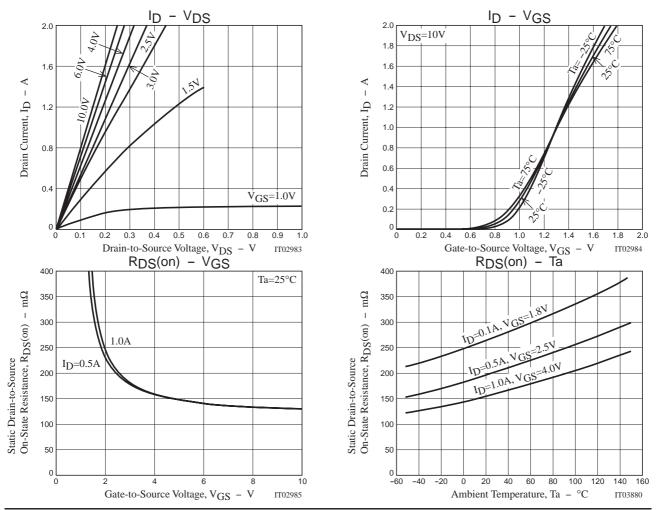
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

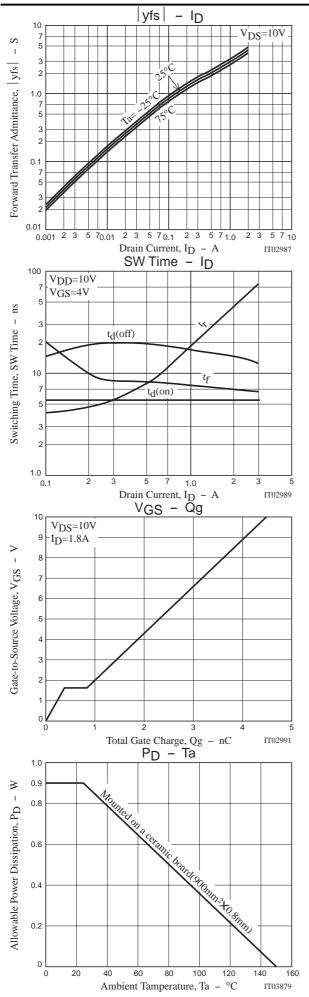
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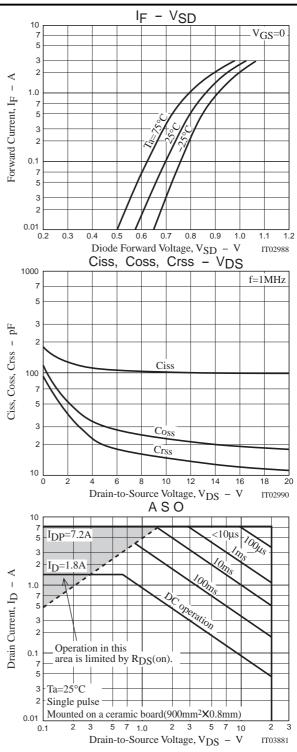
Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		100		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		22		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		15		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		5.5		ns
Rise Time	tr	See specified Test Circuit.		18		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		17		ns
Fall Time	tf	See specified Test Circuit.		8		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =1.8A		4.5		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =1.8A		0.4		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =1.8A		0.4		nC
Diode Forward Voltage	V _{SD}	I _S =1.8A, V _{GS} =0		0.91	1.2	V

Switching Time Test Circuit









Note on usage : Since the CPH3417 is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.

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